

FIG. 1

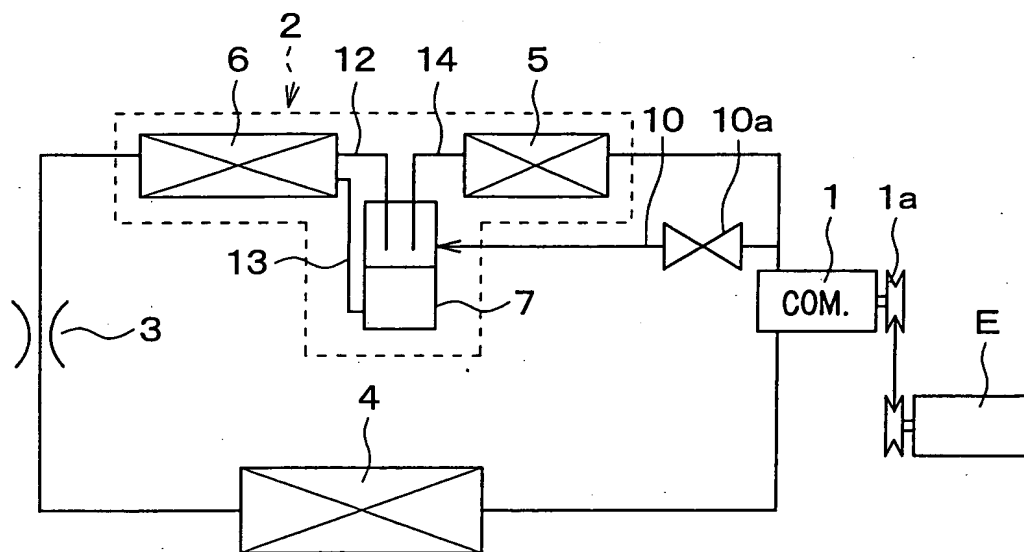
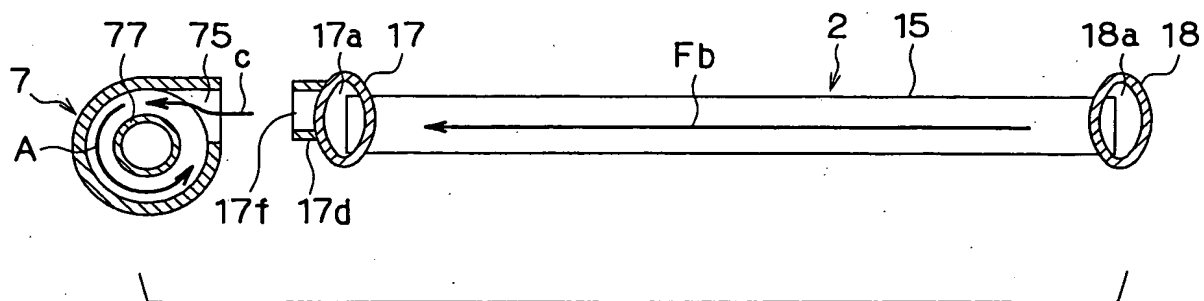


FIG. 3



**FIG. 2**

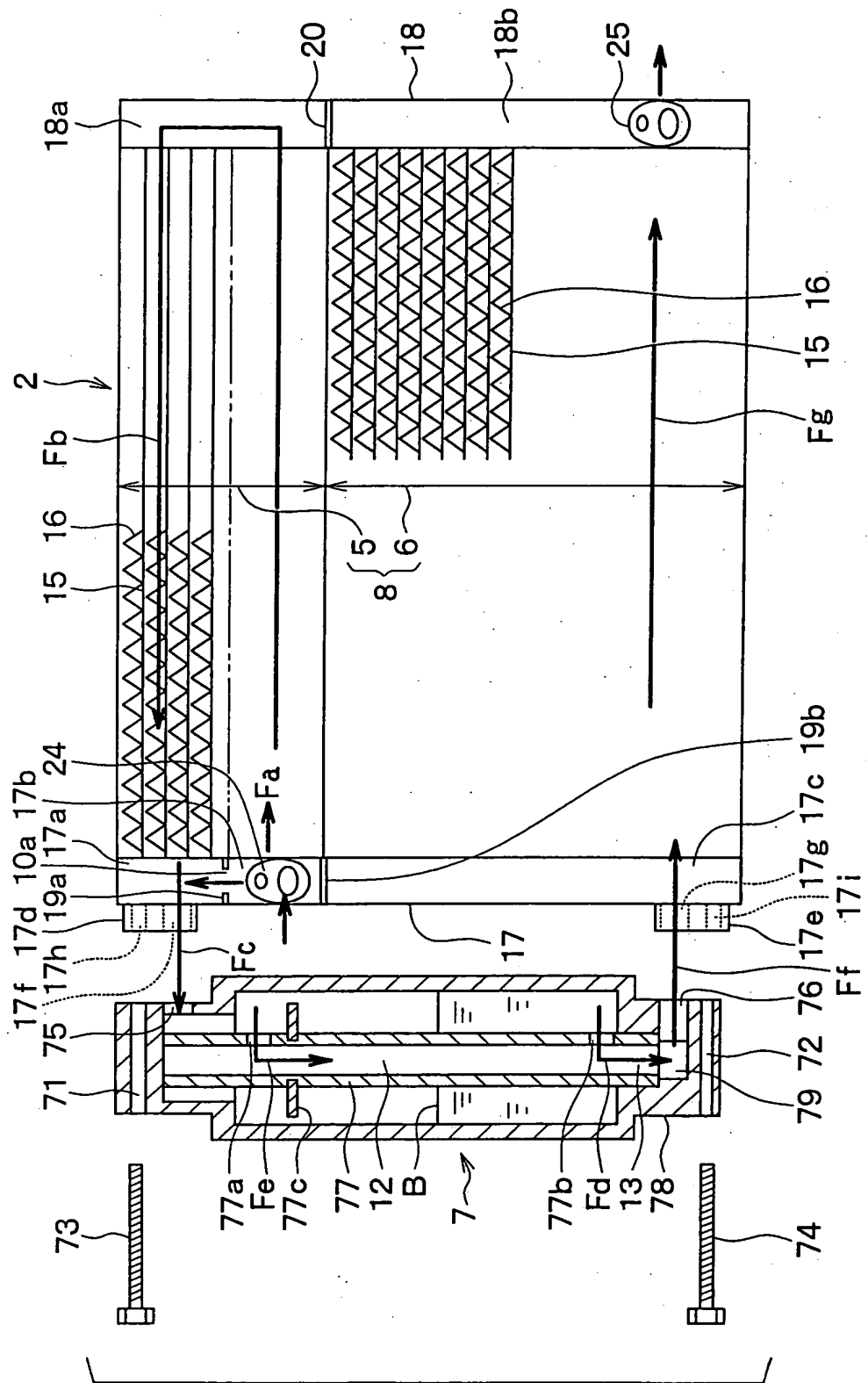




FIG. 5

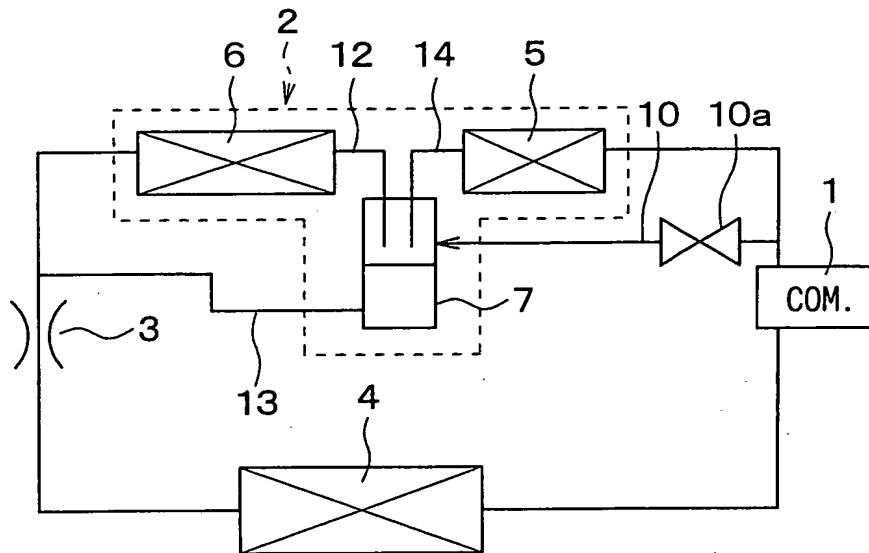
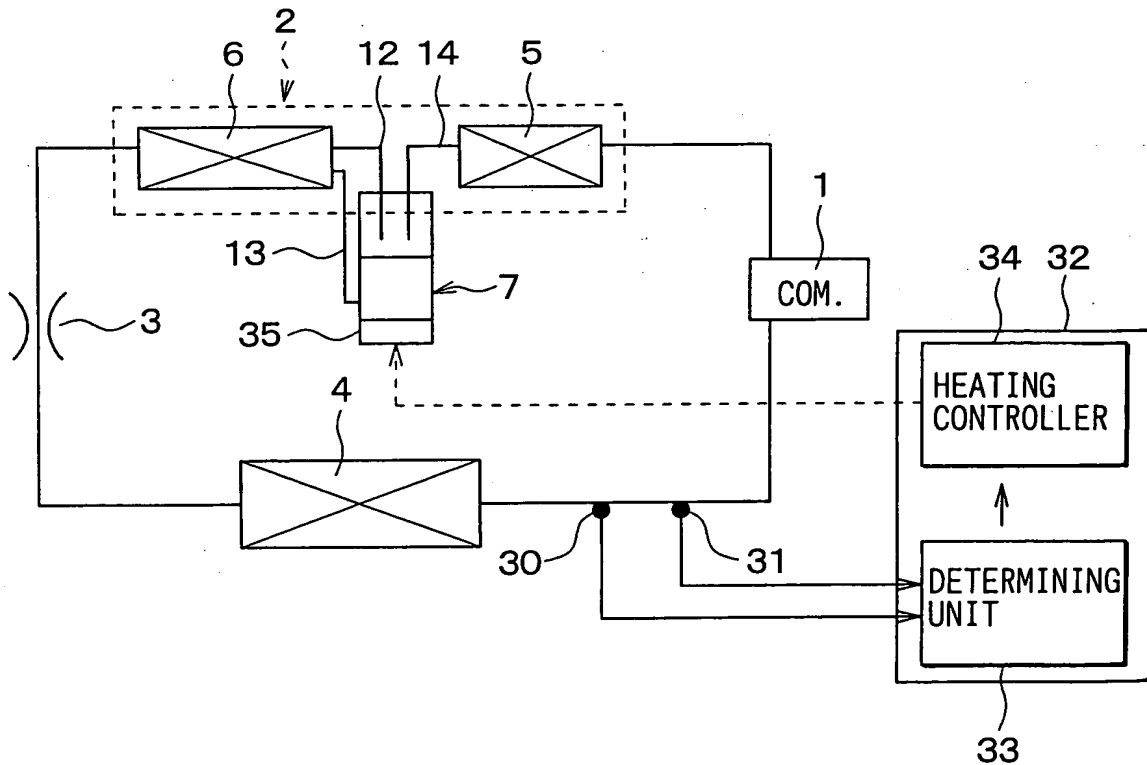
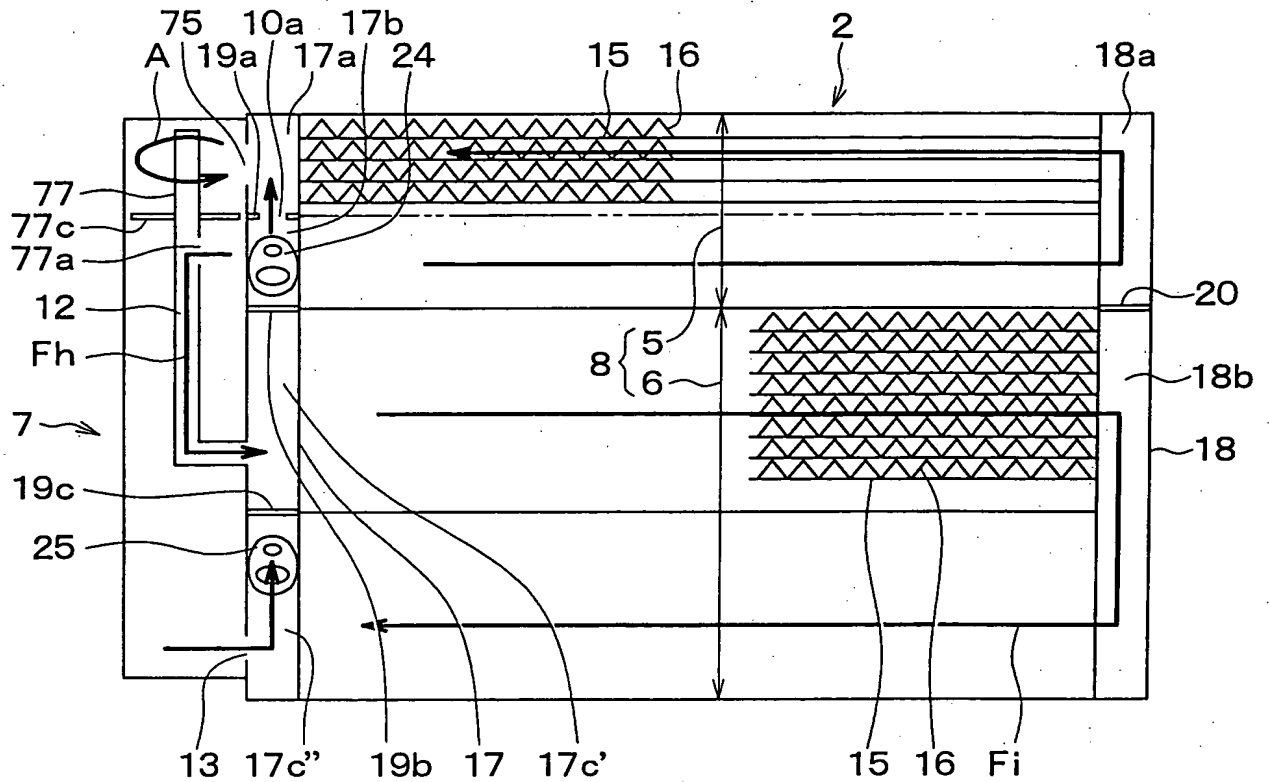


FIG. 7



**FIG. 6A**



**FIG. 6B**

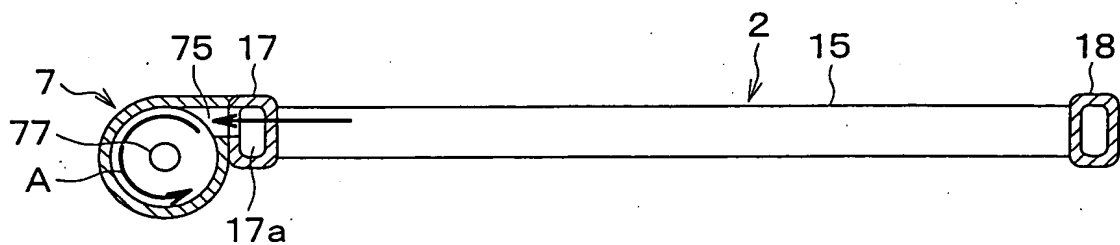


FIG. 8

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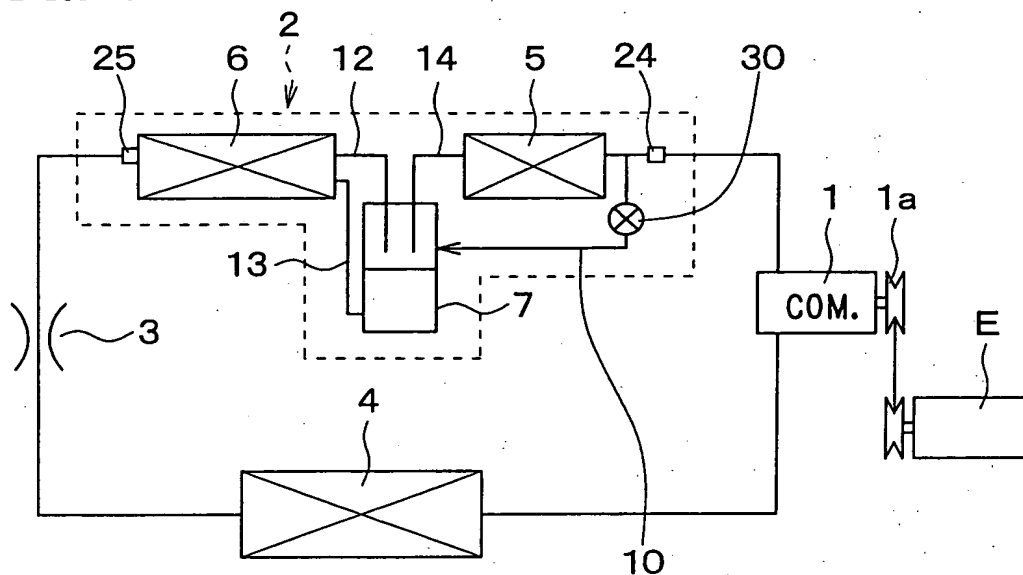


FIG. 9

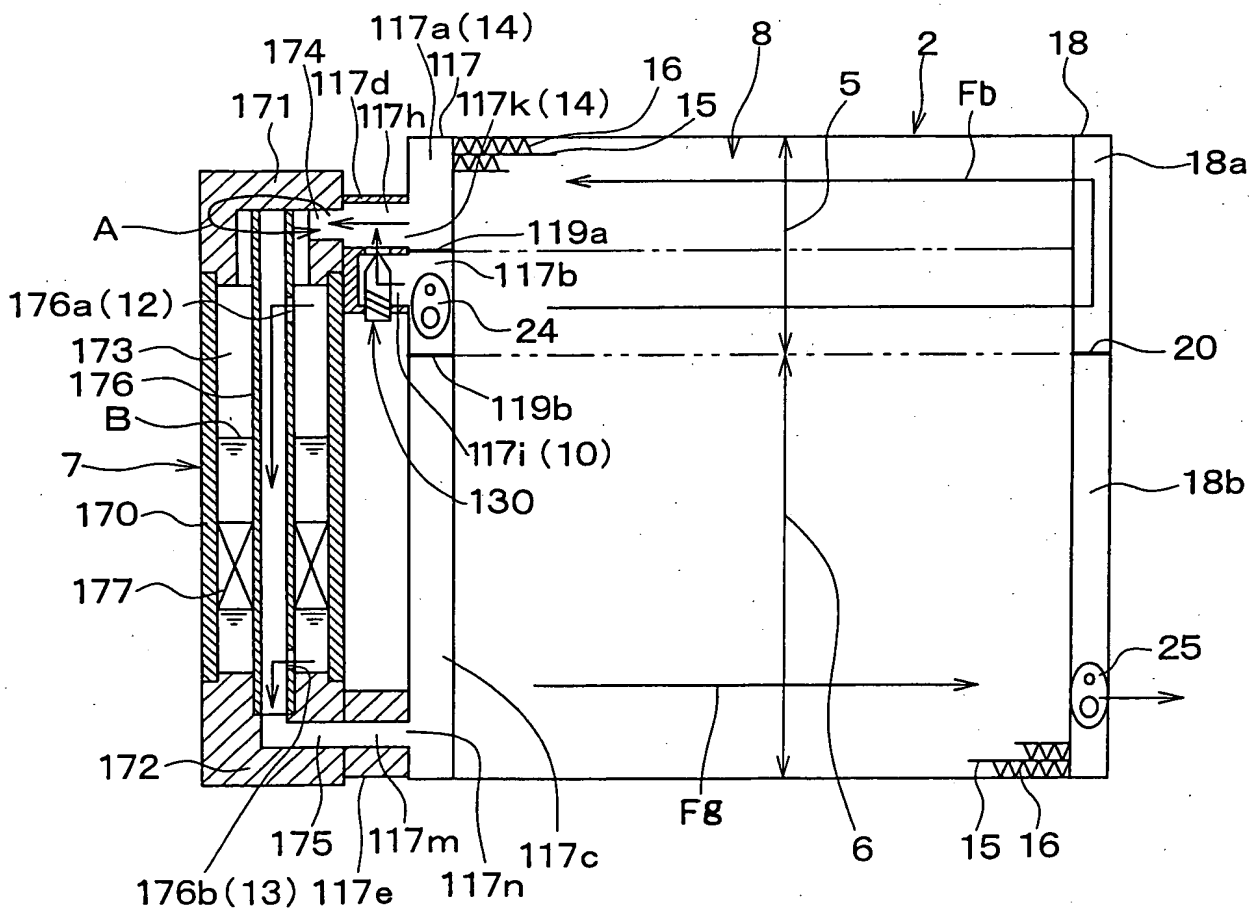


FIG. 10

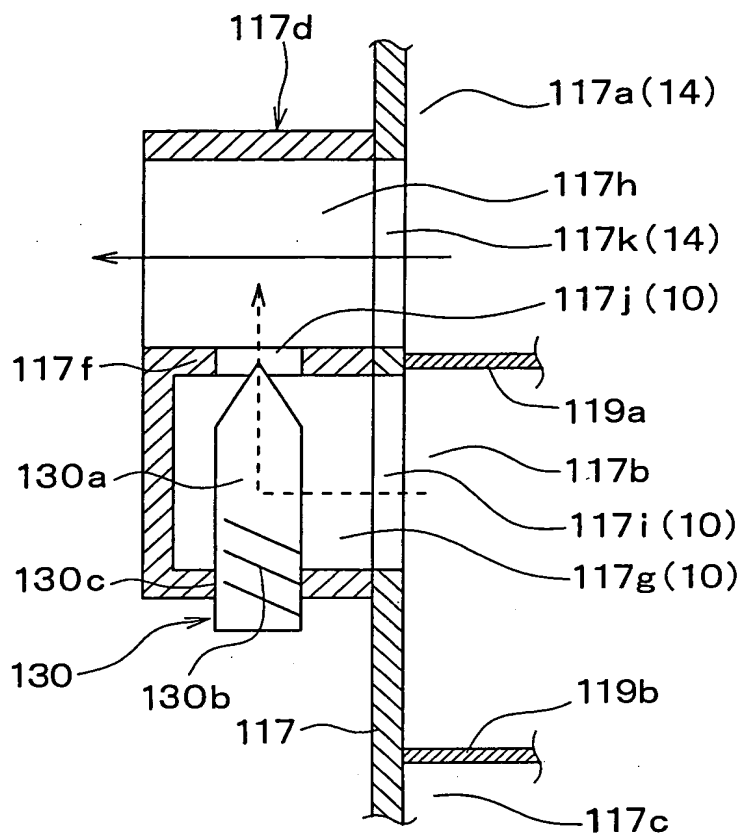
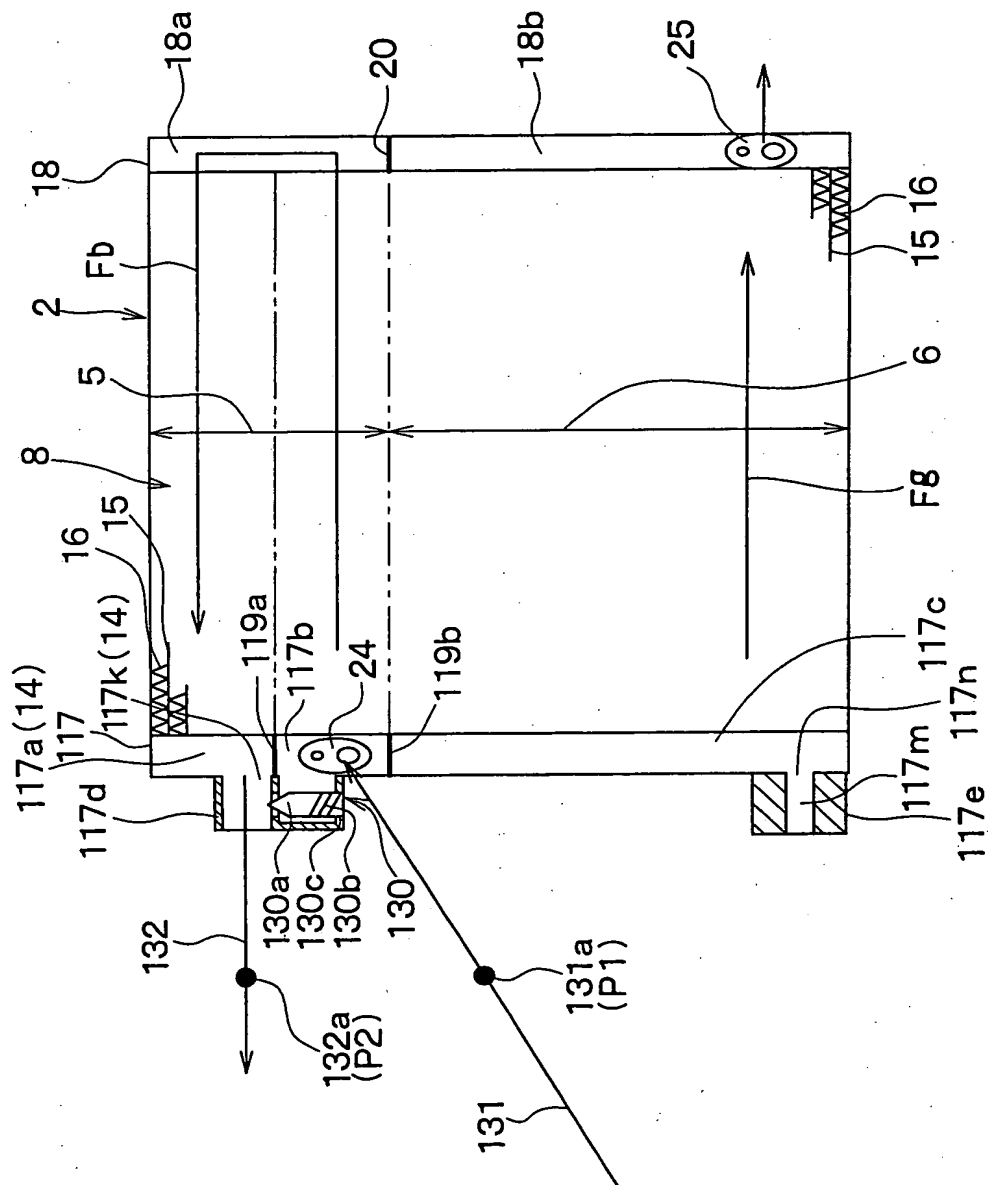
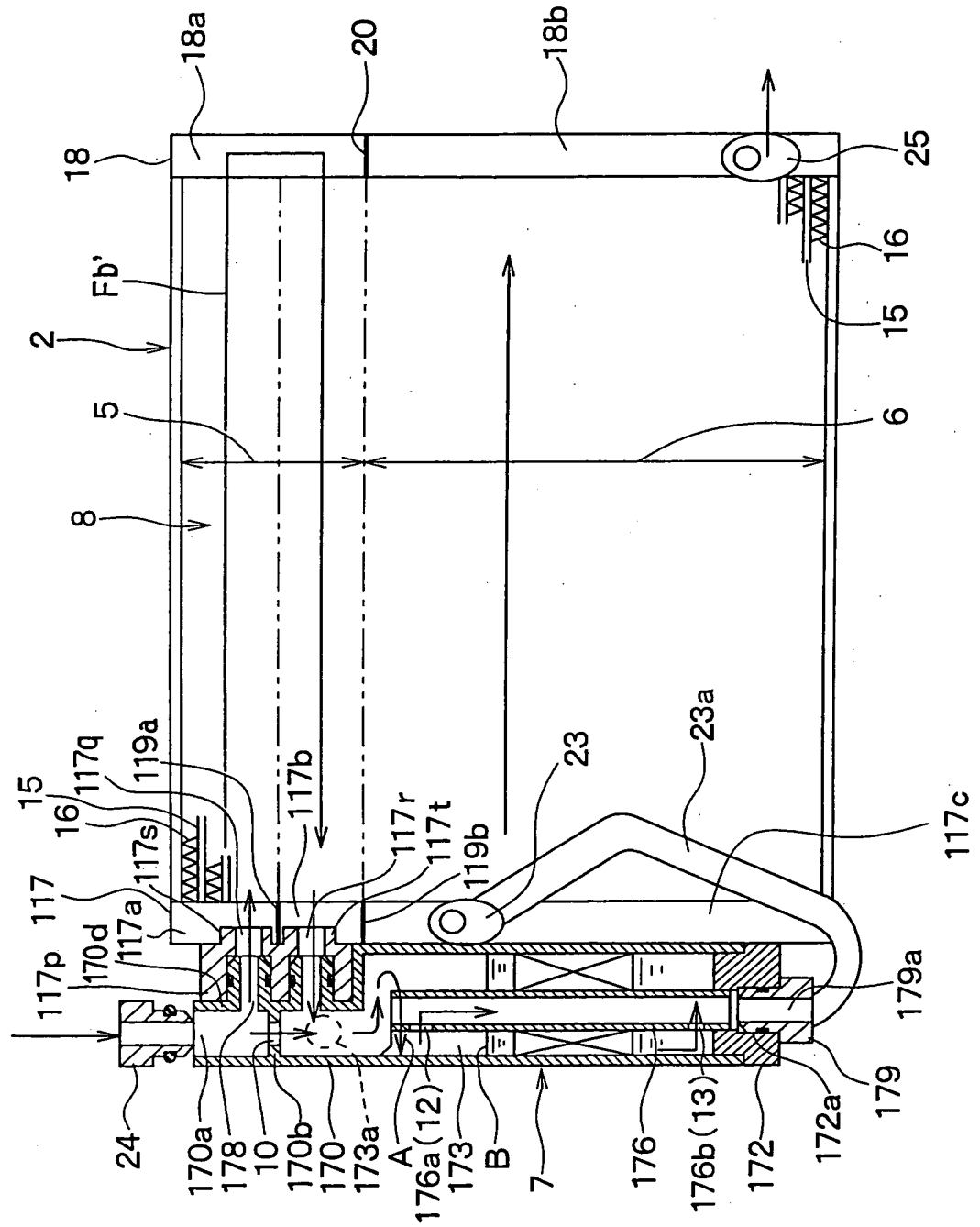


FIG. 11



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FIG. 12



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FIG. 13

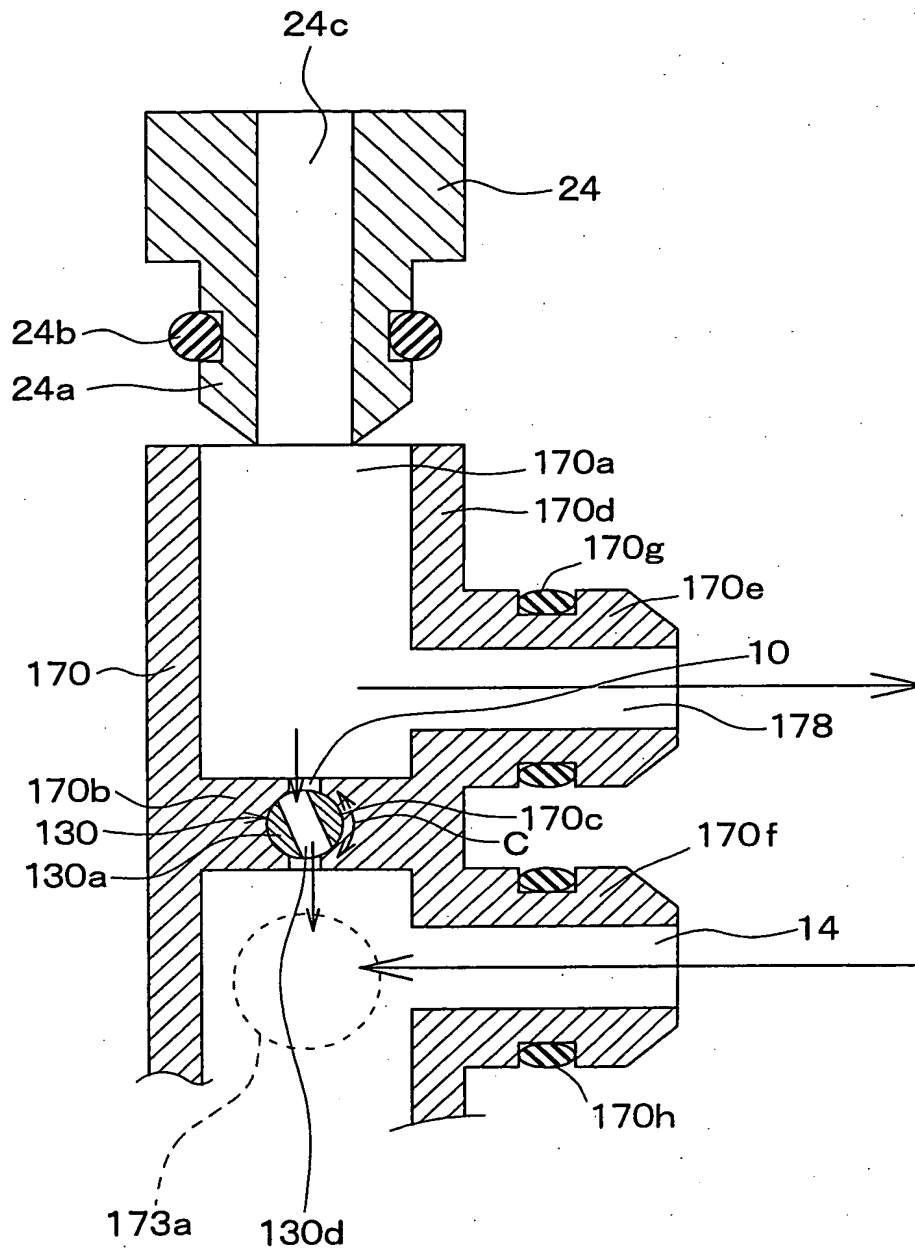
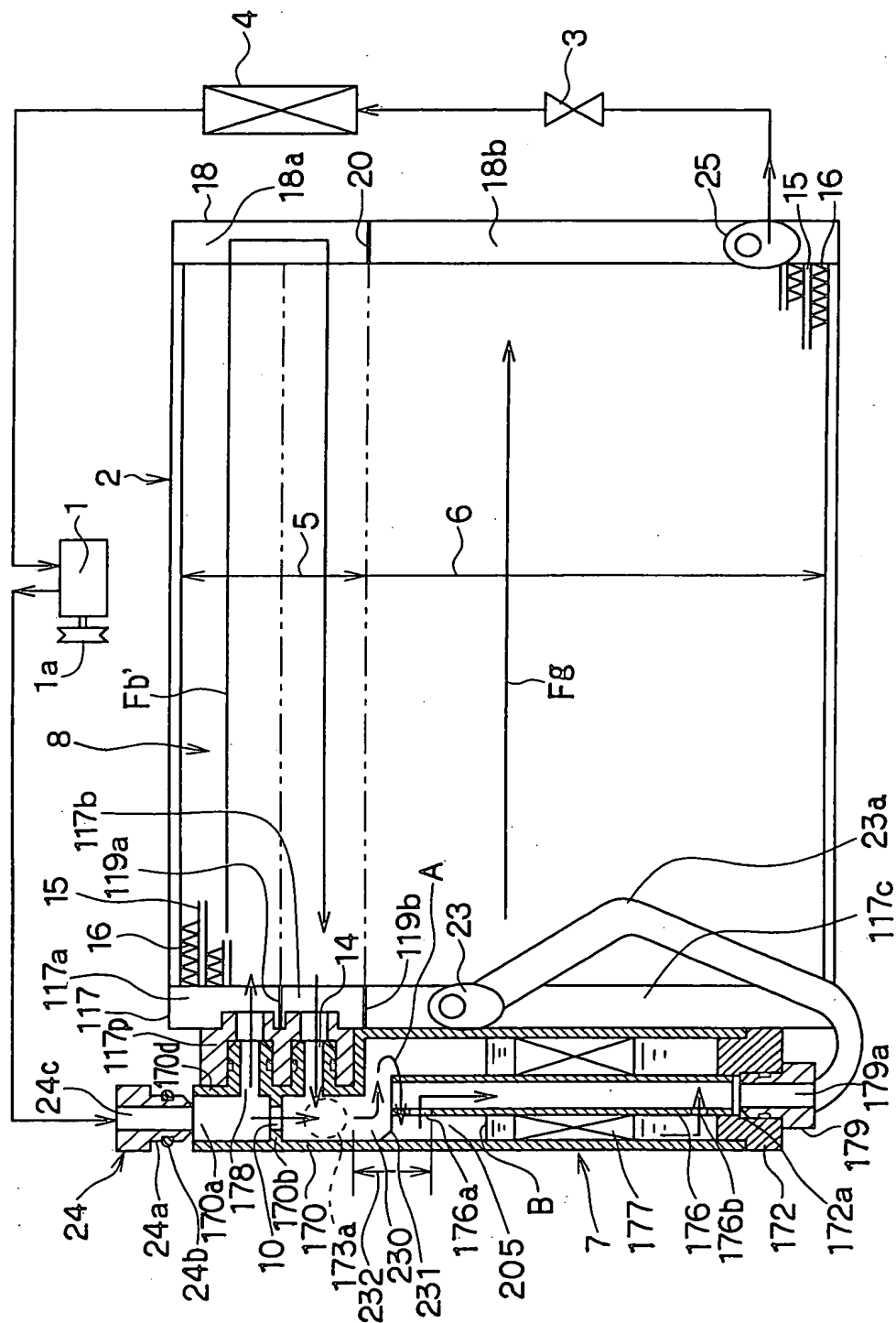


FIG. 14



A cross-sectional view of a semiconductor device. A central vertical channel or well is formed in a substrate 10. The top of the device features a stack of layers labeled 24c, 24, 24a, and 24b. Two small circular features, possibly vias or contacts, are located at the base of this stack. The main body of the device consists of several horizontal layers and regions. On the left side, labels 117a, 10, 170b, and 170 point to different parts of the structure. On the right side, labels 170g, 117p, 117s, 170e, 117q, 178, 117r, and 117t identify specific layers and regions. At the bottom, a dashed circle indicates a feature labeled 173a, which is connected to a layer labeled 14. Other bottom labels include 170h and 170f.

FIG. 16

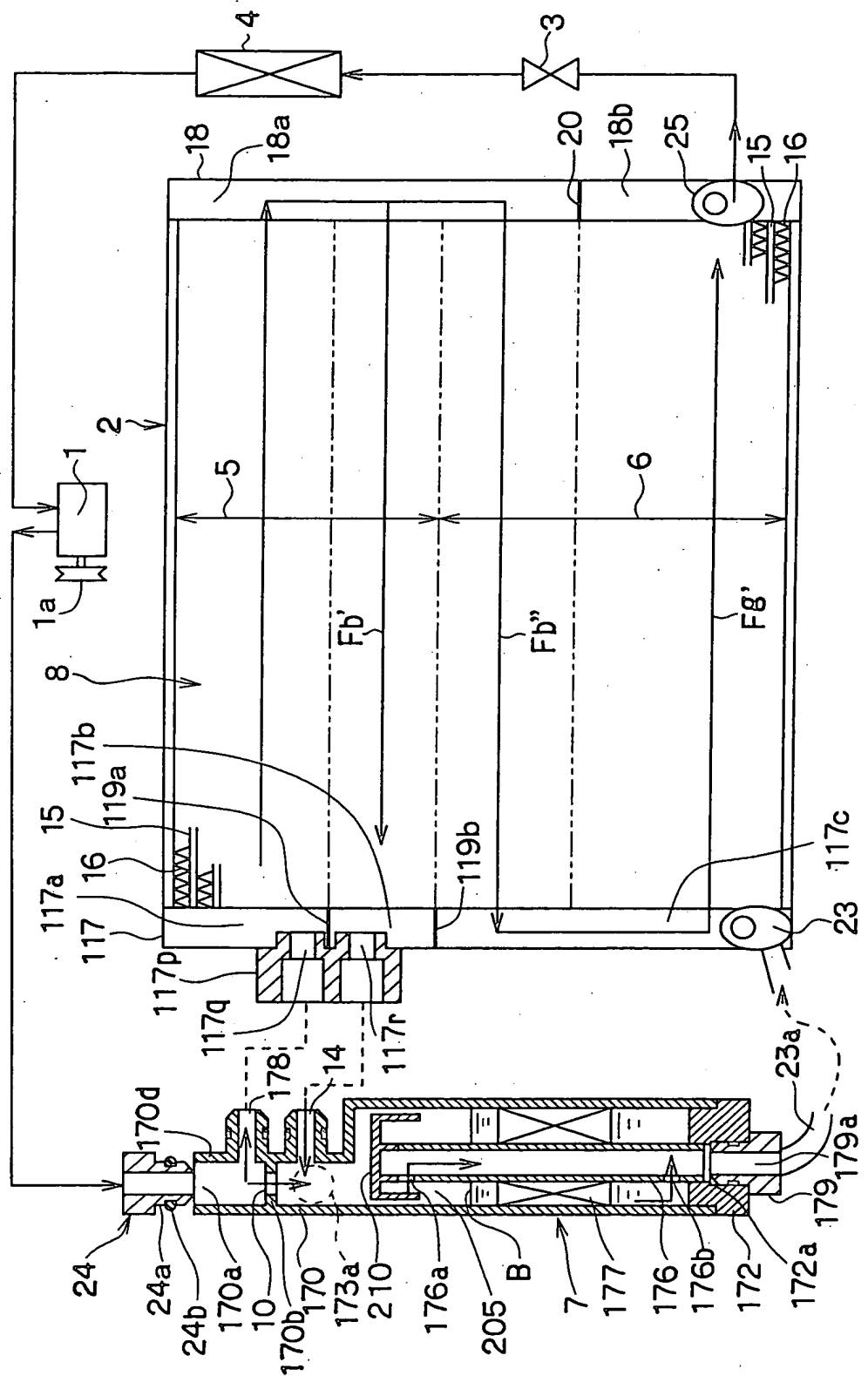
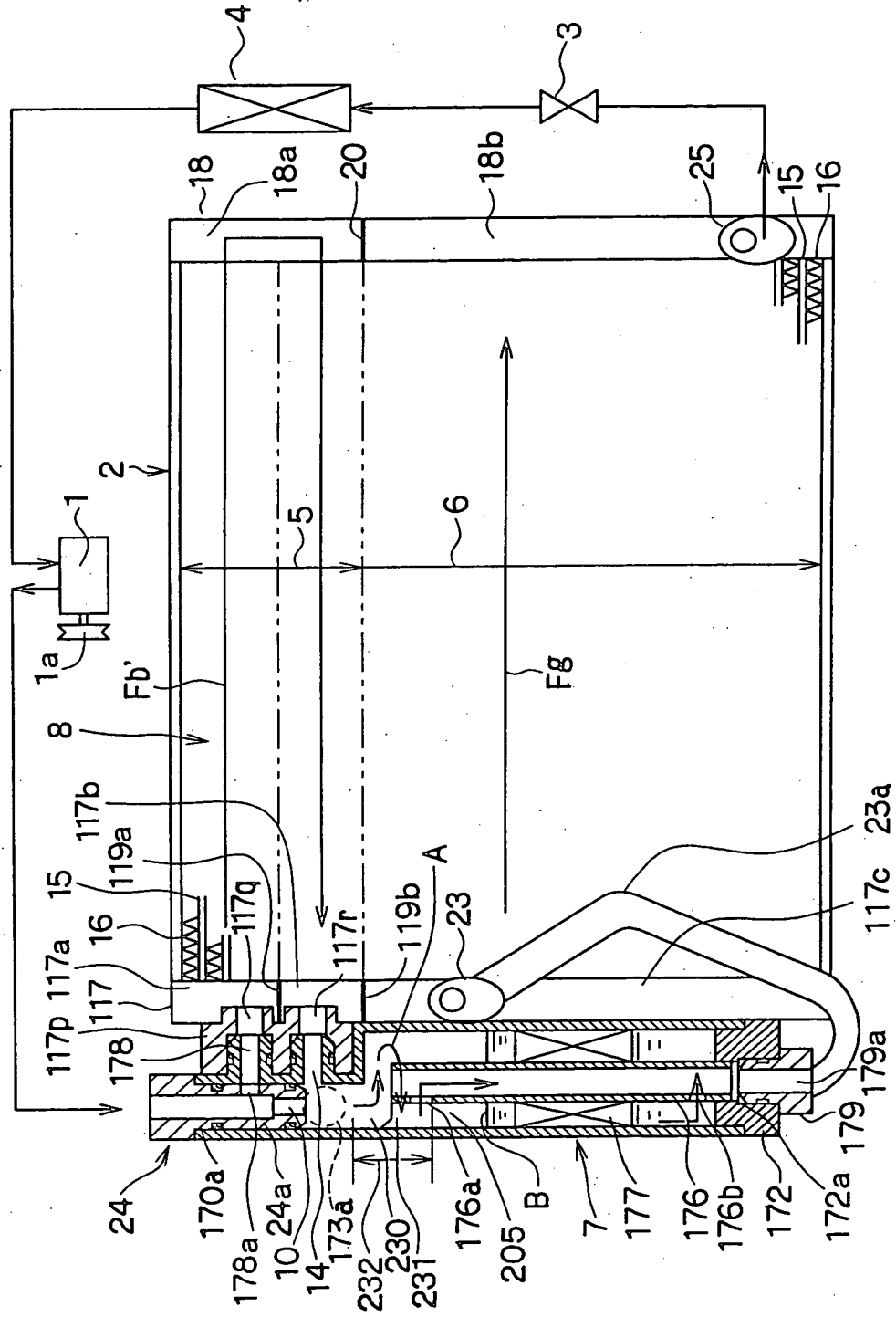
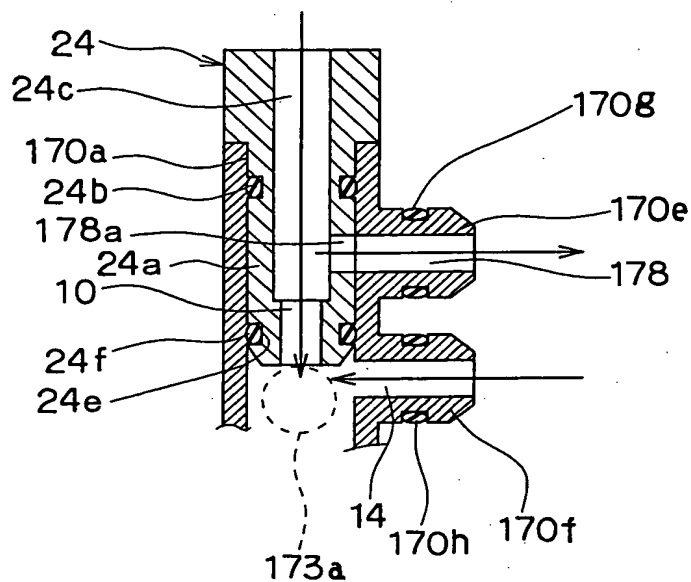


FIG. 17



**FIG. 18**



**FIG. 19** PRIOR ART

